

MOCVD in cross comparison with UHV e-beam evaporation as deposition techniques of EUV multilayers

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Metal/Silicon multilayers (e.g. Mo/Si) have been prepared by means of different techniques such as MOCVD and e-beam evaporation in UHV, with and without ion polishing, at room temperature as well as at optimised higher temperatures. The contribution gives a status report of these different techniques used and presents in cross comparison the measured data of their characterization by use of EUV- and X-ray reflectivity, TEM cross sections etc.